NCD57001

Isolated High Current IGBT Gate Driver

NCD57001 is a high−current single channel IGBT driver with internal galvanic isolation, designed for high system efficiency and reliability in high power applications. Its features include complementary inputs, open drain FAULT and Ready outputs, active Miller clamp, accurate UVLOs, DESAT protection, and soft turn−off at DESAT. NCD57001 accommodates both 5 V and 3.3 V signals on the input side and wide bias voltage range on the driver side including negative voltage capability. NCD57001 provides > 5 kVrms (UL1577 rating) galvanic isolation and > 1200 V_{iorm} (working voltage) capabilities. NCD57001 is available in the wide−body SOIC−16 package with guaranteed 8 mm creepage distance between input and output to fulfill reinforced safety insulation requirements.

Features

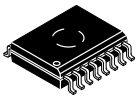
- High Current Output (+4/−6 A) at IGBT Miller Plateau Voltages
- Low Output Impedance for Enhanced IGBT Driving
- Short Propagation Delays with Accurate Matching
- Active Miller Clamp to Prevent Spurious Gate Turn−on
- DESAT Protection with Programmable Delay
- Negative Voltage (Down to −9 V) Capability for DESAT
- Soft Turn Off During IGBT Short Circuit
- IGBT Gate Clamping During Short Circuit
- IGBT Gate Active Pull Down
- Tight UVLO Thresholds for Bias Flexibility
- Wide Bias Voltage Range including Negative VEE2
- 3.3 V to 5 V Input Supply Voltage
- Designed for AEC−Q100 Certification
- 5000 V Galvanic Isolation (to meet UL1577 Requirements)
- 1200 V Working Voltage (per VDE0884−10 Requirements)
- High Transient Immunity
- High Electromagnetic Immunity
- These Devices are Pb−Free, Halogen Free and are RoHS Compliant

Typical Applications

- Solar Inverters
- Motor Control
- Uninterruptible Power Supplies (UPS)
- Industrial Power Supplies
- Welding

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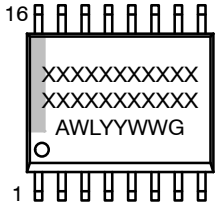
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SOIC−16 WB
CASE 751G−03

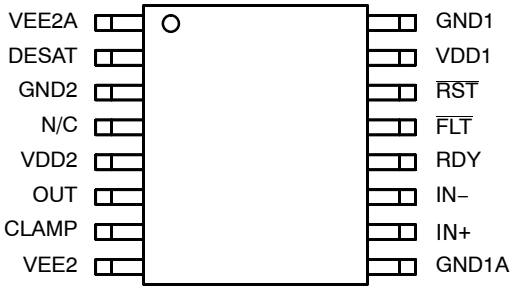
MARKING DIAGRAM



XXXXX	= Specific Device Code
A	= Assembly Location
WL	= Wafer Lot
YY	= Year
WW	= Work Week
G	= Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

PIN ASSIGNMENT



ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

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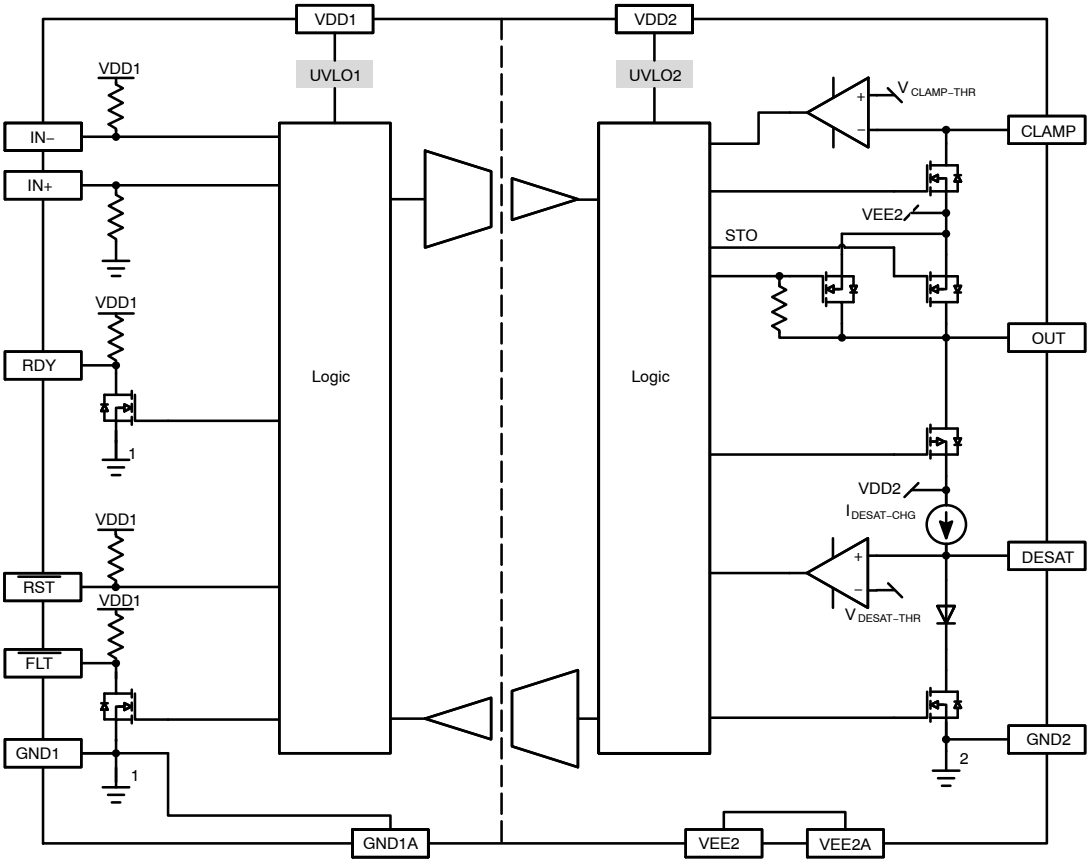


Figure 1. Simplified Block Diagram

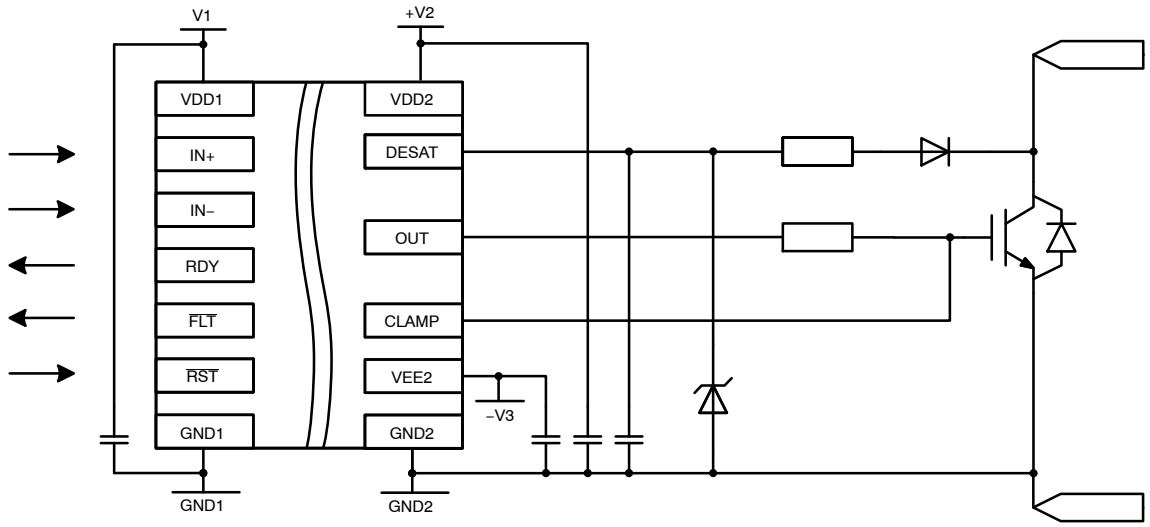


Figure 2. Simplified Application Schematics

PIN DESCRIPTION

Pin Name	No.	I/O	Description
V_{EE2A}	1	Power	Output side negative power supply. A good quality bypassing capacitor is required from these pins to GND2 and should be placed close to the pins for best results. Connect it to GND2 for unipolar supply application.
V_{EE2}	8		
DESAT	2	I/O	Input for detecting the desaturation of IGBT due to a short circuit condition. An internal constant current source $I_{DESAT-CHG}$ charging an external capacitor connected to this pin allows a programmable blanking delay every ON cycle before DESAT fault is processed, thus preventing false triggering. When the DESAT voltage goes up and reaches $V_{DESAT-THR}$, the output is driven low. Further, the /FLT output is activated, please refer to Figure 5 on page 9. A 5 μs mute time apply to IN+ and IN− once DESAT occurs.
GND2	3	Power	Output side gate drive reference connecting to IGBT emitter or FET source.
N/C	4	−	Not connected.
V_{DD2}	5	Power	Output side positive power supply. The operating range for this pin is from UVLO2 to its maximum allowed value. A good quality bypassing capacitor is required from this pin to GND2 and should be placed close to the pins for best results.
OUT	6	O	Driver output that provides the appropriate drive voltage and source/sink current to the IGBT/FET gate. OUT is actively pulled low during start−up and under Fault conditions.
CLAMP	7	I/O	Provides clamping for the IGBT/FET gate during the off period to protect it from parasitic turn−on. Its internal N FET is turned on when the voltage of this pin falls below V_{EE2} + $V_{CLAMP-THR}$. It is to be tied directly to IGBT/FET gate with minimum trace length for best results.
GND1	9	Power	Input side ground reference.
	16		
IN+	10	I	Non inverted gate driver input. It is internally clamped to V_{DD1} and has a pull−down resistor of 50 kΩ to ensure that output is low in the absence of an input signal. A minimum positive going pulse−width is required at IN+ before OUT responds.
IN−	11	I	Inverted gate driver input. It is internally clamped to V_{DD1} and has a pull−up resistor of 50 kΩ to ensure that output is low in the absence of an input signal. A minimum negative going pulse−width is required at IN− before OUT responds.
RDY	12	O	Power good indication output, active high when V_{DD2} is good. There is an internal 50 kΩ pull−up resistor connected to this pin. Multiple of them from different drivers can be ”OR”ed together. If a low RDY event is triggered by UVLO2, the maximum low duration for RDY is 200 ns. OUT remains low when RDY is low. Short time delay may apply. See Figure 4 on page 8 for details.
/FLT	13	O	Fault output (active low) that allows communication to the main controller that the driver has encountered a desaturation condition and has deactivated the output.
/RST	14	I	Reset input with an internal 50 kΩ pull−up resistor, active low to reset fault latch.
V_{DD1}	15	Power	Input side power supply (3.3 V to 5 V).

ABSOLUTE MAXIMUM RATINGS (Over operating free−air temperature range unless otherwise noted) (Note 1)

Symbol	Parameter	Minimum	Maximum	Unit
V_{DD1}−GND1	Supply voltage, input side	−0.3	6	V
V_{DD2}−GND2	Positive Power Supply, output side	−0.3	25	V
V_{EE2}−GND2	Negative Power Supply, output side	−10	0.3	V
V_{DD2}−V_{EE2} (V_{MAX2})	Differential Power Supply, output side	0	25	V
V_{OUT}	Gate−driver output voltage	V_{EE2} − 0.3	V_{DD2} + 0.3	V
I_{PK-SRC}	Gate−driver output sourcing current (maximum pulse width = 10 μs, maximum duty cycle = 0.2%, V_{MAX2} = 20 V)	−	7.8	A
I_{PK-SNK}	Gate−driver output sinking current (maximum pulse width = 10 μs, maximum duty cycle = 0.2%, V_{MAX2} = 20 V)	−	7.1	A
$I_{PK-CLAMP}$	Clamp sinking current (maximum pulse width = 10 μs, maximum duty cycle = 0.2%, V_{CLAMP} = 3 V)	−	2.5	A
t_{CLP}	Maximum Short Circuit Clamping Time (I_{OUT_CLAMP} = 500 mA)	−	10	μs
V_{LIM}−GND1	Voltage at IN+, IN−, /RST, /FLT, RDY	−0.3	V_{DD1} + 0.3	V
I_{LIM}−GND1	Output current of /FLT, RDY	−	10	mA
V_{DESAT}−GND2	Desat Voltage (Note 2)	−9	V_{DD2} + 0.3	V
V_{CLAMP}−GND2	Clamp Voltage	V_{EE2} − 0.3	V_{DD2} + 0.3	V
P_D	Power Dissipation (Note 3)	−	1400	mW
V_{ISO}	Input to Output Isolation Voltage	−1200	1200	V
$T_{J(max)}$	Maximum Junction Temperature	−40	150	°C
T_{STG}	Storage Temperature Range	−65	150	°C
ESD_{HBM}	ESD Capability, Human Body Model (Note 4)	−	±2	kV
ESD_{CDM}	ESD Capability, Charged Device Model (Note 4)	−	±2	kV
MSL	Moisture Sensitivity Level	−	2	−
T_{SLD}	Lead Temperature Soldering Reflow, Pb−Free Versions (Note 5)	−	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.
2. The minimum value is verified by characterization with a single pulse of 100 mA for 100 μs.
3. The value is estimated for ambient temperature 25°C and junction temperature 150°C, 650 mm^2, 1 oz copper, 2 surface layers and 2 internal power plane layers. Power dissipation is affected by the PCB design and ambient temperature.
4. This device series incorporates ESD protection and is tested by the following methods:
   ESD Human Body Model tested per AEC−Q100−002 (EIA/JESD22−A114)
   ESD Charged Device Model tested per AEC−Q100−011 (EIA/JESD22−C101)
   Latchup Current Maximum Rating: ≤100 mA per JEDEC standard: JESD78, 25°C
5. For information, please refer to our Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

THERMAL CHARACTERISTICS

Symbol	Parameter	Conditions	Value	Unit
$R_{\theta JA}$	Thermal Resistance, Junction−to−Air	100 mm^2, 1 oz Copper, 1 Surface Layer	150	°C/W
		650 mm^2, 1 oz Copper, 2 Surface Layers and 2 Internal Power Plane Layers	84	

OPERATING RANGES (Note 6)

Symbol	Parameter	Min	Max	Unit
V_{DD1}–GND1	Supply voltage, input side	UVLO1	5.5	V
V_{DD2}–GND2	Positive Power Supply, output side	UVLO2	24	V
V_{EE2}–GND2	Negative Power Supply, output side	−10	0	V
V_{DD2}–V_{EE2} (V_{MAX2})	Differential Power Supply, output side	0	24	V
V_{IL}	Low level input voltage at IN+, IN−, /RST	0	0.3 X V_{DD1}	V
V_{IH}	High level input voltage at IN+, IN−, /RST	0.7 X V_{DD1}	V_{DD1}	V
$\lvert dV_{ISO}/dt \rvert$	Common Mode Transient Immunity (1500 V)	100	–	kV/μs
T_A	Ambient Temperature	−40	125	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

6. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.

ELECTRICAL CHARACTERISTICS (V_{DD1} = 5 V, V_{DD2} = 15 V, V_{EE2} = −8 V. For typical values T_A = 25°C, for min/max values, T_A is the operating ambient temperature range that applies, unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
VOLTAGE SUPPLY						
$V_{UVLO1-OUT-ON}$	UVLO1 Output Enabled		–	–	3	V
$V_{UVLO1-OUT-OFF}$	UVLO1 Output Disabled		2.4	–	–	V
$V_{UVLO1-HYST}$	UVLO1 Hysteresis		0.125	–	–	V
$V_{UVLO2-OUT-ON}$	UVLO2 Output Enabled		13.2	13.5	13.8	V
$V_{UVLO2-OUT-OFF}$	UVLO2 Output Disabled		12.2	12.5	12.8	V
$V_{UVLO2-HYST}$	UVLO2 Hysteresis		–	1		V
I_{DD1-0}	Input Supply Quiescent Current Output Low	IN+ = Low, IN− = Low RDY = High, /FLT = High	–	1	2	mA
$I_{DD1-100}$	Input Supply Quiescent Current Output High	IN+ = High, IN− = Low RDY = High, /FLT = High	–	4.8	6	mA
I_{DD2-0}	Output Positive Supply Quiescent Current, Output Low	IN+ = Low, IN− = Low RDY = High, /FLT = High, no load	–	3.3	4	mA
$I_{DD2-100}$	Output Positive Supply Quiescent Current, Output High	IN+ = High, IN− = Low RDY = High, /FLT = High, no load	–	3.6	6	mA
I_{EE2-0}	Output Negative Supply Quiescent Current, Output Low	IN+ = High, IN− = Low, no load	–	0.4	2	mA
$I_{EE2-100}$	Output Negative Supply Quiescent Current, Output High	IN+ = High, IN− = Low, no load	–	0.2	2	mA
LOGIC INPUT AND OUTPUT						
V_{IL}	IN+, IN−, /RST Low Input Voltage		–	–	0.3 x V_{DD1}	V
V_{IH}	IN+, IN−, /RST High Input Voltage		0.7 x V_{DD1}	–	–	V
$V_{IN-HYST}$	Input Hysteresis Voltage		–	0.15 x V_{DD1}	–	V
I_{IN-L}, I_{RST-L}	IN−, /RST Input Current (50 kΩ pull−up resistor)	V_{IN-}/V_{RST} = 0 V	–	−100	–	μA
I_{IN+H}	IN+ Input Current (50 kΩ pull−down resistor)	V_{IN+} = 5 V	–	100	–	μA

ELECTRICAL CHARACTERISTICS (V_{DD1} = 5 V, V_{DD2} = 15 V, V_{EE2} = −8 V. For typical values T_A = 25°C, for min/max values, T_A is the operating ambient temperature range that applies, unless otherwise noted) (continued)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
LOGIC INPUT AND OUTPUT						
I_{RDY-L}, I_{FLT-L}	RDY, /FLT Pull−up Current (50 kΩ pull−up resistor)	V_{RDY}/V_{FLT} = Low	–	100	–	μA
V_{RDY-L}, V_{FLT-L}	RDY, /FLT Low Level Output Voltage	I_{RDY}/I_{FLT} = 5 mA	–	–	0.3	V
t_{MIN1}	Input Pulse Width of IN+, IN− for No Response at Output		–	–	10	ns
t_{MIN2}	Input Pulse Width of IN+, IN− for Guaranteed Response at Output		40	–	–	ns
$t_{RST-MIN}$	Pulse Width of /RST for Resetting /FLT		800	–	–	ns
DRIVER OUTPUT						
V_{OUTL1}	Output Low State (V_{OUT} − V_{EE2})	I_{SINK} = 200 mA	–	0.1	0.2	V
V_{OUTL3}		I_{SINK} = 1.0 A, T_A = 25°C	–	0.5	0.8	
V_{OUTH1}	Output High State (V_{DD2} − V_{OUT})	I_{SRC} = 200 mA	–	0.3	0.5	V
V_{OUTH3}		I_{SRC} = 1.0 A, T_A = 25°C	–	0.8	1	
$I_{PK-SNK1}$	Peak Driver Current, Sink (Note 7)	V_{OUT} = 7.9 V	–	7.1	–	A
$I_{PK-SRC1}$	Peak Driver Current, Source (Note 7)	V_{OUT} = −5 V	–	7.8	–	A
MILLER CLAMP						
V_{CLAMP}	Clamp Voltage (V_{CLAMP} − V_{EE2})	I_{CLAMP} = 2.5 A, T_A = 25°C	–	1.3	1.7	V
		I_{CLAMP} = 2.5 A, T_A = −40°C to 125°C	–	–	3	
$V_{CLAMP-THR}$	Clamp Activation Threshold (V_{CLAMP} − V_{EE2})		1.5	2	2.5	V
IGBT SHORT CIRCUIT CLAMPING						
$V_{CLAMP-OUT}$	Clamping Voltage, (V_{OUT} − V_{DD2})	IN+ = Low, IN− = High, I_{OUT} = 500 mA (pulse test, t_{CLPmax} = 10 μs)	–	0.9	1.1	V
$V_{CLAMP-CLAMP}$	Clamping Voltage, Clamp (V_{CLAMP} − V_{DD2})	IN+ = High, IN− = Low, $I_{CLAMP-CLAMP}$ = 500 mA (pulse test, t_{CLPmax} = 10 μs)	–	1.4	1.6	V
DESAT PROTECTION						
$V_{DESAT-THR}$	DESAT Threshold Voltage		8.5	9	9.5	V
$V_{DESAT-NEG}$	DESAT Negative Voltage	I_{DESAT} = 1.5 mA	–	−8	–	V
$I_{DESAT-CHG}$	Blanking Charge Current	V_{DESAT} = 7 V	0.45	0.5	0.6	mA
$I_{DESAT-DIS}$	Blanking Discharge Current		–	50	–	mA
DYNAMIC CHARACTERISTICS						
t_{PD-ON}	IN+, IN− to Output High Propagation Delay	C_{LOAD} = 10 nF V_{IH} to 10% of output change for PW > 150 ns. OUT and CLAMP pins are connected together	40	60	90	ns
t_{PD-OFF}	IN+, IN− to Output Low Propagation Delay	C_{LOAD} = 10 nF V_{IL} to 90% of output change for PW > 150 ns. OUT and CLAMP pins are connected together	40	66	90	ns
$t_{DISTORT}$	Propagation Delay Distortion (= t_{PD-ON} − t_{PD-OFF})	T_A = 25°C, PW > 150 ns	−15	−6	15	ns
		T_A = −40°C to 125°C, PW > 150 ns	−25	–	25	
$t_{DISTORT_TOT}$	Prop Delay Distortion between Parts	PW > 150 ns	−30	0	30	ns

ELECTRICAL CHARACTERISTICS (V_{DD1} = 5 V, V_{DD2} = 15 V, V_{EE2} = −8 V. For typical values T_A = 25°C, for min/max values, T_A is the operating ambient temperature range that applies, unless otherwise noted) (continued)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS						
t_{RISE}	Rise Time (see Fig. 3) (Note 7)	C_{LOAD} = 1 nF, 10% to 90% of Output Change	–	10	–	ns
t_{FALL}	Fall Time (see Fig. 3) (Note 7)	C_{LOAD} = 1 nF, 90% to 10% of Output Change	–	15	–	ns
t_{LEB}	DESAT Leading Edge Blanking Time (See Fig. 5)		–	450	–	ns
t_{FILTER}	DESAT Threshold Filtering Time (see Fig. 5)		–	320	–	ns
t_{STO}	Soft Turn Off Time (see Fig. 5)	C_{LOAD} = 10 nF, R_G = 10 Ω. V_{EE2} = 0 V	–	1.8	–	μs
		C_{LOAD} = 10 nF, R_G = 10 Ω	–	2.6	–	
t_{FLT}	Delay after t_{FILTER} to /FLT		–	450	–	ns
t_{RST}	/RST Rise to /FLT Rise Delay		–	23	–	ns
t_{RDY1O}	RDY High to Output High Delays (see Fig. 4)		–	55	–	ns
t_{RDY2O}						
t_{RDY1F}	$V_{UVLO2-OUT-OFF}$ to RDY Low Delays (see Fig. 4)		–	8	–	μs
t_{RDY2F}						

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

7. Values based on design and/or characterization.

ORDERING INFORMATION

Device	Package Type	Shipping†
NCD57001DWR2G	SOIC−16 Wide Body (Pb−Free)	1,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

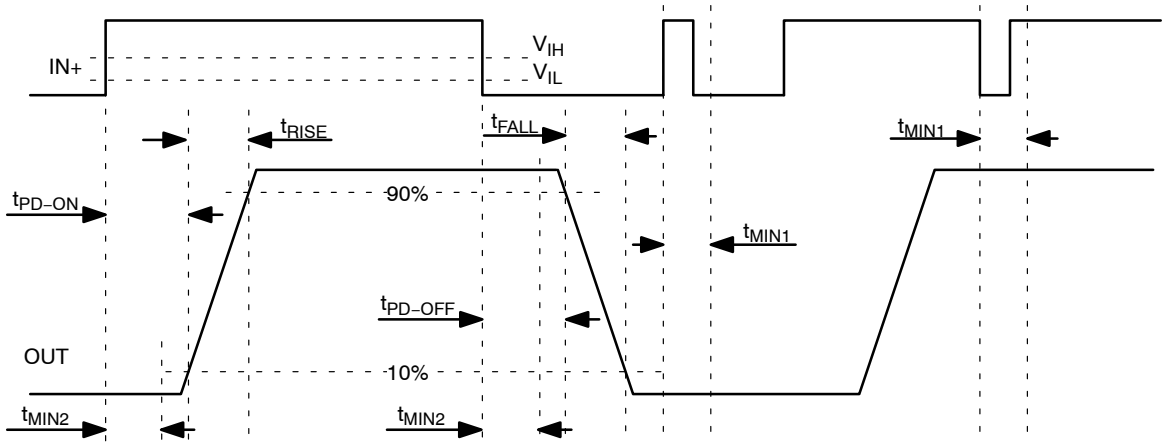


Figure 3. Propagation Delay, Rise and Fall Time

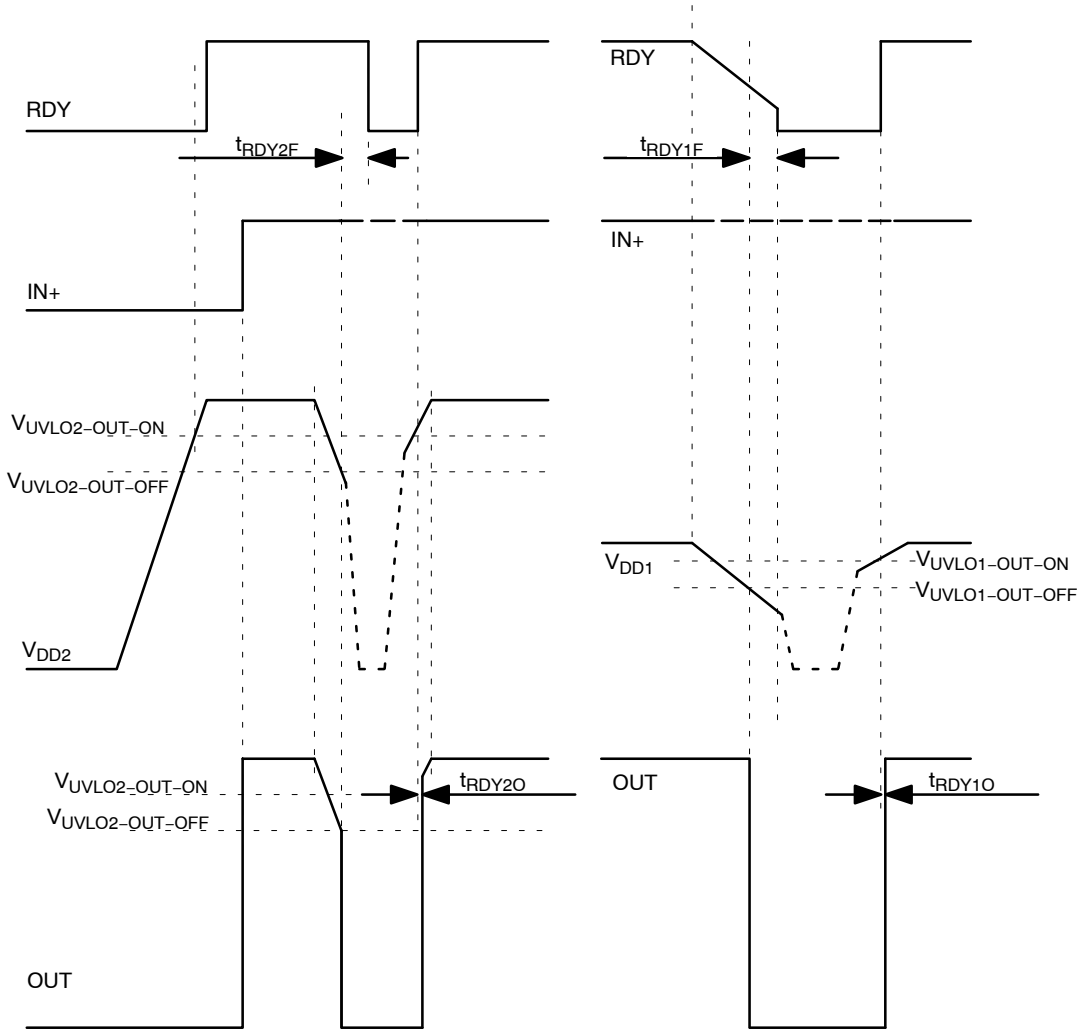


Figure 4. UVLO Waveform

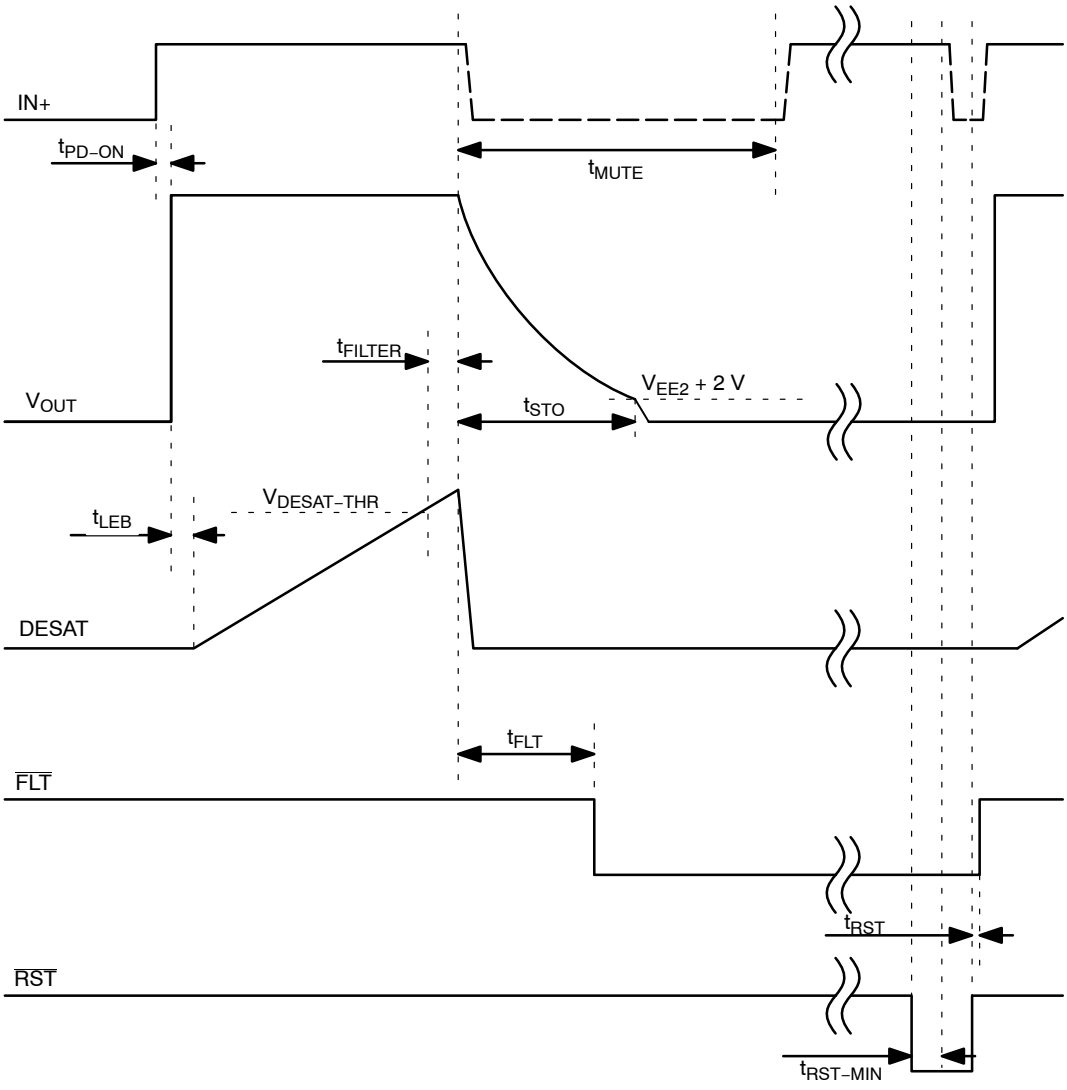


Figure 5. DESAT Response Waveform

TYPICAL CHARACTERISTICS

(Conditions for the following figures are the same as stated for ELECTRICAL CHARACTERISTICS Table unless otherwise noted. Typical and/or average values are used.)

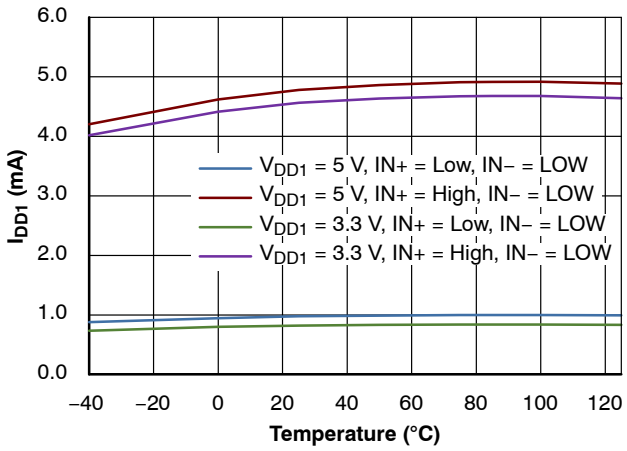


Figure 6. V_{DD1} Supply Current

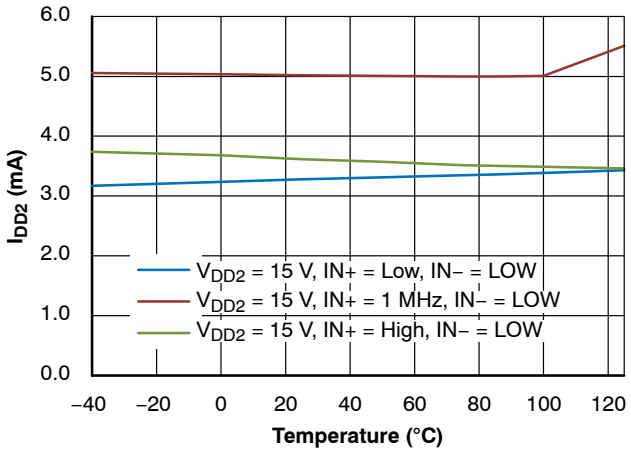


Figure 7. V_{DD2} Supply Current

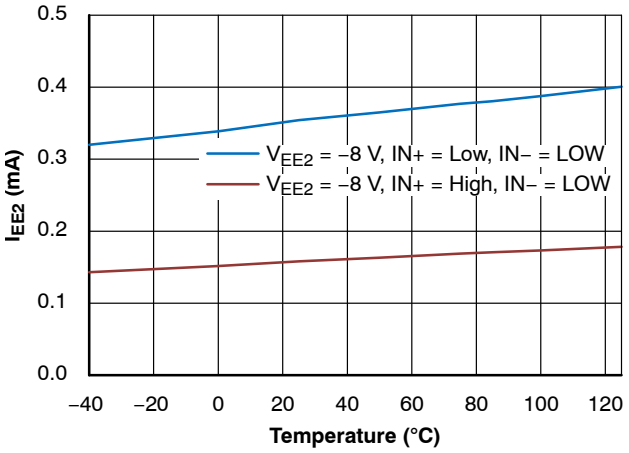


Figure 8. V_{EE2} Supply Current

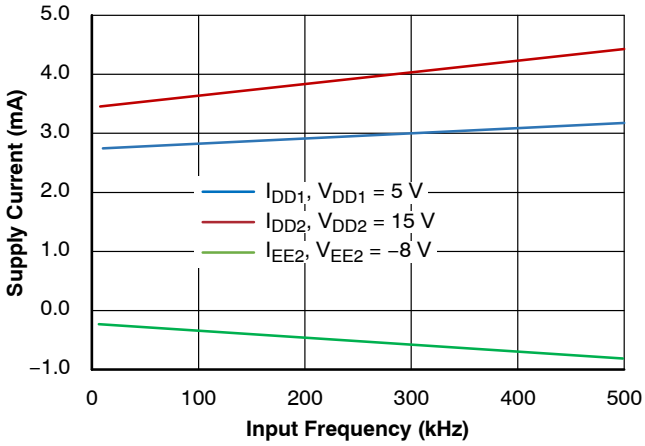


Figure 9. Supply Current vs Frequency

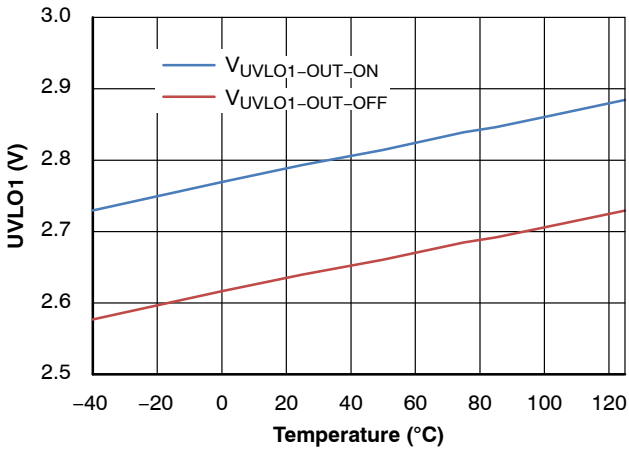


Figure 10. UVLO1 Threshold Voltage

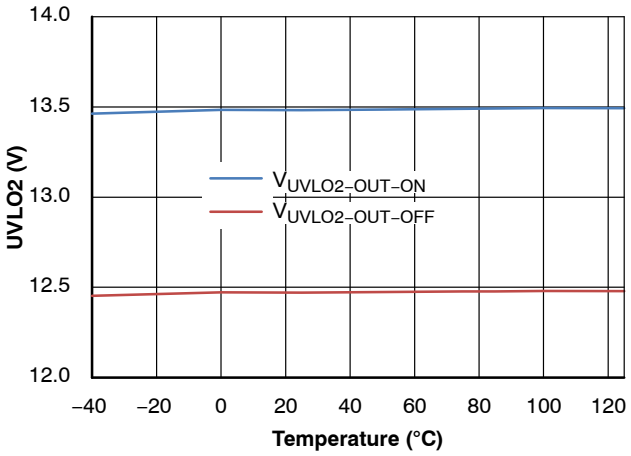


Figure 11. UVLO2 Threshold Voltage

TYPICAL CHARACTERISTICS

(Conditions for the following figures are the same as stated for ELECTRICAL CHARACTERISTICS Table unless otherwise noted. Typical and/or average values are used.) (continued)

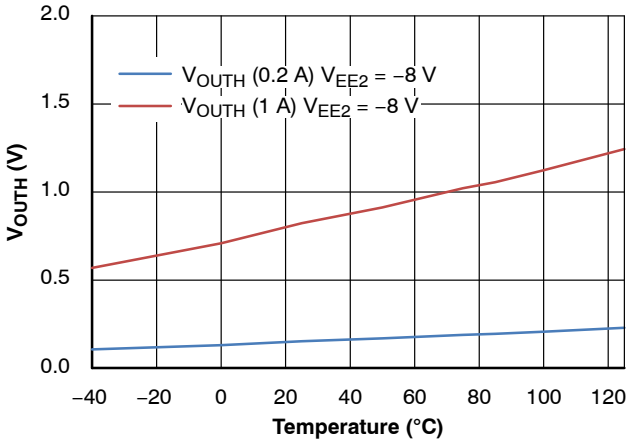


Figure 12. Output Voltage Drop, Sourcing

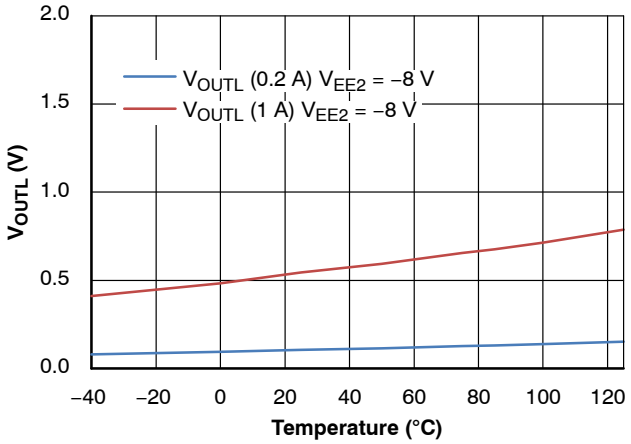


Figure 13. Output Voltage Drop, Sinking

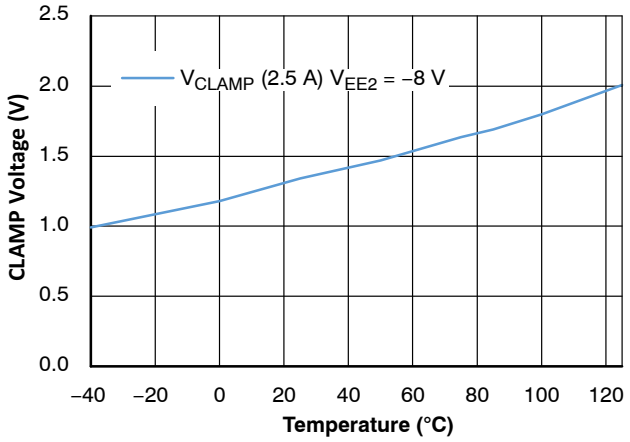


Figure 14. CLAMP Voltage Drop

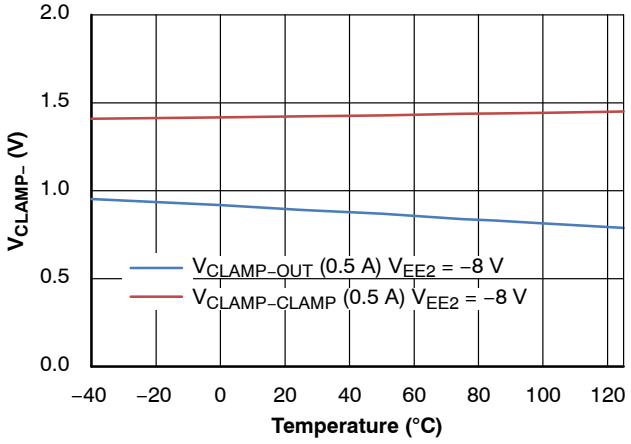


Figure 15. IGBT Short Circuit Clamp Voltage Drop

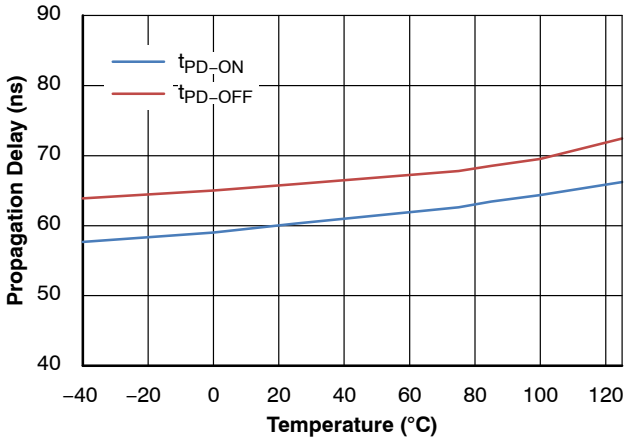


Figure 16. Propagation Delay

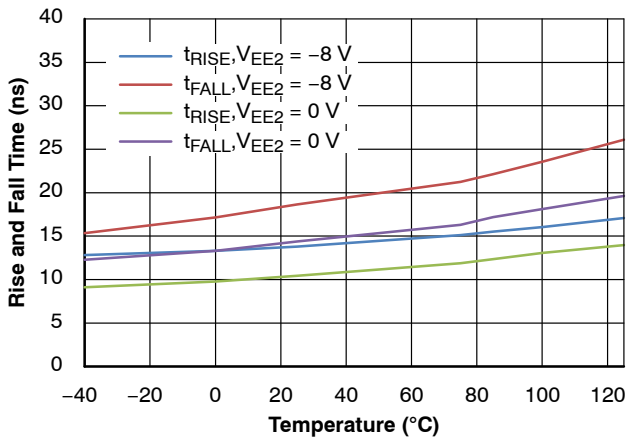


Figure 17. Rise and Fall Time

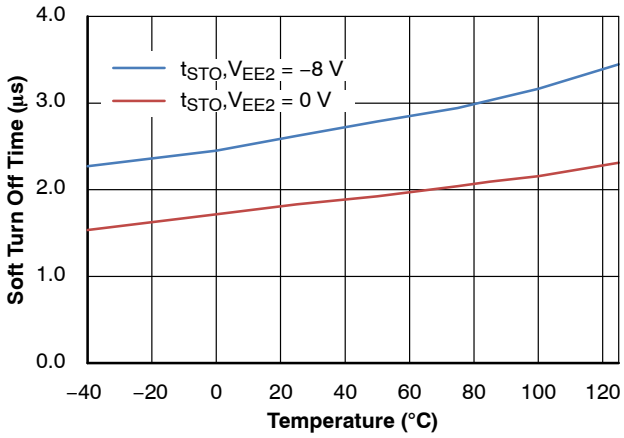
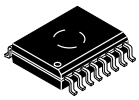


Figure 18. Soft Turn Off Time

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

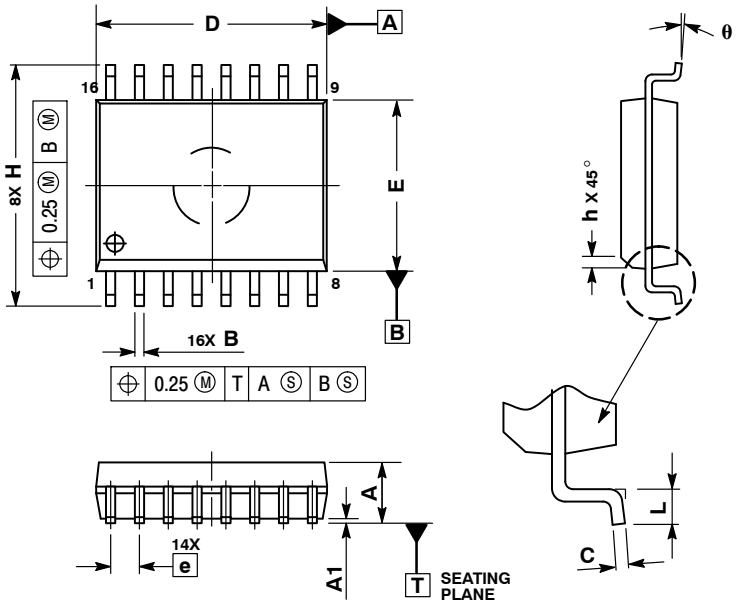
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1
SCALE 1:1

SOIC−16 WB
CASE 751G−03
ISSUE D

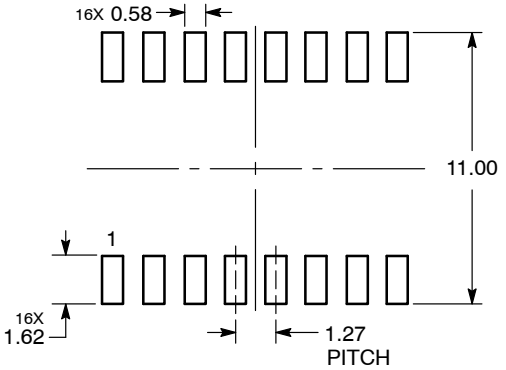
DATE 12 FEB 2013



NOTES:
1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
3. DIMENSIONS D AND E DO NOT INLCUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF THE B DIMENSION AT MAXIMUM MATERIAL CONDITION.

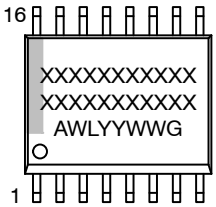
	MILLIMETERS	
DIM	MIN	MAX
A	2.35	2.65
A1	0.10	0.25
B	0.35	0.49
C	0.23	0.32
D	10.15	10.45
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.25	0.75
L	0.50	0.90
q	0 °	7 °

SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
YY = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

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DESCRIPTION:	**SOIC−16 WB**	**PAGE 1 OF 1**

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